(After the 37 CFR 1.97(b) time period, but before final action or notice of allowance, whichever occurs first) under 37 CFR 1.97(d) together with: []a Statement under 37 CFR 1.97(e), as checked below, and a \$180.00 fee under 37 CFR 1.17(p), or

(Filed after final action or notice of allowance, whichever occurs first, but on or before payment of the issue fee)

under 37 CFR 1.97(i): Applicant requests that the IDS and cited reference(s) be placed in the application filewrapper. (Filed after payment of issue fee)

Staten	nent Un	der 37 CFR 1.97(e)		
[]	any co	tem of information contained in this Information Disclosure Statement was first cited in mmunication from a foreign patent office in a counterpart foreign application not more tree months prior to the filing of this Information Disclosure Statement; or		
[]	No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned, after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.			
Staten	nent Un	der 37 CFR 1.704(d) (Patent Term Adjustment) Applies to original applications (other than design) filed on or after May 29, 2000		
[]	comm was no	tem of information contained in the Information Disclosure Statement was cited in a unication from a foreign patent office in a counterpart application and this communication of treceived by any individual designated in § 1.56(c) more than thirty days prior to the of the Information Disclosure Statement.		
[X]	Enclos	sed herewith is form PTO-1449:		
	[]	Copies of the cited references are enclosed.		
		[X] Since this application was filed after June 30, 2003, copies of issued U.S. patents and published U.S. applications are not required and are not being provided.		
	[]	Copies of the cited references are enclosed except those entered in prior application, U.S. Application No. [], to which priority under 35 U.S.C. 120 is claimed. [The earlier application contains copies of the cited references.]		
	[]	The listed references were cited in the enclosed International Search Report in a counterpart foreign application.		
	[]	The "concise explanation" requirement (non-English references) for reference(s) [under 37 CFR 1.98(a)(3) is satisfied by:		
		[] the explanation provided on the attached sheet.		
		[] the explanation provided in the Specification.		
		[] submission of the enclosed International Search Report.		
		submission of the enclosed English-language version of a foreign Search Report and/or foreign Office Action.		
		[] the enclosed English language abstract.		

[]	Appli	cant requests that the following r	non-published pending application	cations be considered:
Examiner's Initials	s			
	-	U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
	_	U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
		U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
		Examiner	Date	_
	[]	A copy of each above-cited app	plication, including the curre	ent claims, is enclosed.
	[]	A copy of each above-cited app those entered in prior application 35 U.S.C. 120 is claimed.	plication, including the curre on, U.S. Application No. [ent claims, is enclosed, except], to which priority under
		er is requested to return a copy of ere considered with the next office		plications indicating which
It is re	equeste	d that the information disclosed h	nerein be made of record in t	his application.
Metho	od of pa	nyment:		
[]		eck for the fee noted above is enc npanying Reply. A copy of this S		cluded in the check with the
[]	Please	e charge Deposit Account 08-038 sed.	30 in the amount of \$[]. A copy of this Statement is
[X]	Please	e charge any deficiency in fees ar	nd credit any overpayment to	Deposit Account 08-0380.
		I	Respectfully submitted,	
		I	HAMILTON, BROOK, SMI	TH & REYNOLDS, P.C.
]	Caroline M. Fleming Registration No.: 45,566 Telephone: (978) 341-0136 Facsimile: (978) 341-0136	Eling

Concord, MA 01742-9133 Dated: 1/2/04

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PTO-1449 REPRODUCED	ATTORNEY DOCKET NO. 2037.2038-001		lication no. 64 7, 664	
INFORMATION DISCLOSURE CITATIONS IN AN APPLICATION	FIRST NAMED INVENTOR Tony Mai		FILING DATE August 25,	2003
(Use several sheets if necessary)	EXAMINER	2135	RMATION NO.	GROUP 2631
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U.S. PATENT DOCUMENTS						
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT		
/E.B.	' AA	6,314,052 B2	11/06/01	Foss et al.		
20000000	AB	6,314,150 B1	11/06/01	Vowe		
90000000	AC	6,330,296 B1	12/11/01	Atallah et al.		
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/E.B.	/ AF	6,549,041 B2	04/15/03	Waldrop		
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EXAMINER /Emmanuel Bayard/	DATE CONSIDERED 02/25/2008	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
/E.B./ ^{AR}	C.H. Kim et al. "A 64 Mbit, 640 Mbyte/s bidirectional Data Strobed, Double-Data-Rate SDRAM with a 40-mW DLL for a 256-Mbyte System", <i>IEEE J. Solid State Circuits</i> , 33(11), November 1998.				
/E.B 	Hsiang-Hui Chang et al. "A Wide Range Delay-Locked Loop With a Fixed Latency of One Clock Cycle", IEEE J. Solid State Circuits, 37(8), August 2002.				
/E.B. A T	Hongil Yoon et al. "A 2.5V, 333-Mb/s/pin, 1-Gbit, Double-Data-Rate Synchronous DRAM", <i>IEEE J. Solid State Circuits</i> , 34(11), November 1999.				
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